

L Number	Hits	Search Text	DB	Time stamp
-	17	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and (etch near4 pits or nanotube)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 15:23
-	31	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impurity near10 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 16:27
-	9	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impurity near10 pressure near4 partial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 16:29
-	65	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial same (silane or source or propane or silicon or carbon) and impurity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:44
-	23	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial near10 (silane or source or propane or silicon or carbon) and impurity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:22
-	4	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and block\$4 near3 technique	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:41
-	16	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and block\$5 near10 impurit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:42
-	17	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial same (silane or source or propane or silicon or carbon) and (impur\$4 or contain\$4 or dop\$4) near10 partial adj pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:50
-	10	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial near15 (silane or source or propane or silicon or carbon) and (impur\$4 or contain\$4 or dop\$4) near10 partial adj pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 18:03
-	24	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial near15 (silane or source or propane or silicon or carbon) and (impur\$4 or contain\$4 or dop\$4) near10 (control\$4 or adjust\$4 or prevent\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 18:10
-	2	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and pressure near4 partial near15 (silane or source or propane or silicon or carbon) and impur\$4 same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 18:12
-	57	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impur\$4 same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 18:14
-	27	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impur\$4 near15 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 18:19

-	11	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and prevent\$4 near15 etch\$4 same pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/07 18:21
-	27	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impur\$4 near15 etch\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 12:08
-	62	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impur\$4 near15 (suppress\$4 or prevent\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 12:15
-	26	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and impur\$4 near15 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 12:33
-	80	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and partial adj pressure and impur\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 12:44
-	45	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and micropipe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 12:48
-	16	(sic or silicon adj carbide) near10 (CVD or chemical adj vapor adj deposit\$4) and (micropipe or etch adj pit) same (impur\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 14:21
-	30	(sic or silicon adj carbide) near5 (CVD or chemical adj vapor adj deposit\$4) and partial adj pressure near13 (reactant or silane or propane or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 14:36
-	88	(sic or silicon adj carbide) near5 (CVD or chemical adj vapor adj deposit\$4) and rate same (etch near2 pit or defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 14:58
-	43	(sic or silicon adj carbide) near5 (CVD or chemical adj vapor adj deposit\$4) and unintention\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 15:37
-	7	(chemical adj vapor adj deposit\$4 or CVD) and (impur\$5 same block\$4) same partial adj pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 15:44
-	12	(chemical adj vapor adj deposit\$4 or CVD) and impur\$5 same block\$4 near10 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 15:49
-	7	(chemical adj vapor adj deposit\$4 or CVD) and block\$4 near2 technique same impur\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/08 15:53
-	5	partial adj pressure near15 block\$4 and (chemical adj vapor adj deposit\$4 or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/10 10:11

-	4	partial adj pressure near15 impur\$4 near10 (prevent\$4 or suppress\$4) and (chemical adj vapor adj deposit\$4 or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 10:15
-	29	pressure near15 impur\$4 near10 (prevent\$4 or suppress\$4) and (chemical adj vapor adj deposit\$4 or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 10:26
-	37	block\$4 near4 technique same (impur\$4 or dop\$4) and (chemical adj vapor adj deposit\$4 or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 10:25
-	25	pressure near15 dop\$4 near10 (prevent\$4 or suppress\$4) and (chemical adj vapor adj deposit\$4 or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 10:31
-	35	(chemical adj vapor adj deposit\$4 or cvd) and impurit\$4 near10 incorporat\$4 near10 pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:16
-	29	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:20
-	14	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane same silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:25
-	1	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane same silane same propane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:26
-	4	sic near10 (CVD or chemical adj vapor adj deposit\$4) and tetramethylsilane and silane same propane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:32
-	4	sic near10 (CVD or chemical adj vapor adj deposit\$4) and (tetramethylsilane or "Si(CH.sub.3).sub.4") and (silane or "sih.sub.4") same (propane or "c.sub.3h.sub.8")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:34
-	26	sic near10 (CVD or chemical adj vapor adj deposit\$4) and (tetramethylsilane or "Si(CH.sub.3).sub.4") and (silane or "sih.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:34
-	61	(silicon adj carbide or sic) same (tetramethylsilane or "Si(CH.sub.3).sub.4") and (silane or "sih.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:36
-	41	(silicon adj carbide or sic) same (tetramethylsilane or "Si(CH.sub.3).sub.4") same (silane or "sih.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 13:59
-	29	(heat\$4 or thermal or temperature) near10 rate same defects and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 14:12

-	44	(heat\$4 or thermal or temperature) near10 rate near10 substrate same (sic or silicon adj carbide) and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 14:38
-	58	(heat\$4 or thermal or temperature) near10 rate near10 (rapid\$4 or high\$4) same (sic or silicon adj carbide) and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 14:52
-	2	(heat\$4 or thermal or temperature) near10 rate near10 ramp\$4 same (sic or silicon adj carbide) and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 14:59
-	18	(heat\$4 or thermal or temperature) near10 rate near10 ramp\$4 and (silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:05
-	24	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and ramp\$4 near3 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:08
-	72	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and rate near10 (deposit\$4) near4 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:10
-	38	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and rate near10 (deposit\$4) near4 temperature same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:16
-	3	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD).ti. and (heat\$4 near4 rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:26
-	7	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD).ti. and rate near10 (rapid\$4 or high)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:25
-	11	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD).ti. and rate near5 (temperature or thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:25
-	16	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and (heating near5 rate) same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/10 15:39
-	84	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and (heating near5 rate) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 10:50
-	81	(silicon adj carbide or sic) near5 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near5 temperature near10 (heat\$3 or ramp\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:18
-	59	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near5 temperature near10 (heat\$3 or ramp\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:21

-	13	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near5 thermal near10 (heat\$3 or ramp\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:23
-	12	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) same (rate) near5 (heat\$3 or ramp\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:27
-	45	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near5 (heat\$3 or ramp\$4) same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:31
-	11	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near5 (heat\$3 or ramp\$4) near4 (min or minute)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:34
-	41	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near6 (min or minute) near3 C	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:39
-	56	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near3 C! same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:44
-	11	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near3 C! and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:47
-	7	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near3 (heat\$4 or ramp\$4) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:51
-	23	(silicon adj carbide or sic) near2 (chemical adj vapor adj deposit\$4 or CVD) and (rate) near3 (temperature) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/14 11:51